WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

a lead electrode connecting to a lead wire;

a case electrode having a projecting wall portion around a periphery thereof; and

a semiconductor chip disposed between said lead electrode and said case electrode with a bonding member interposed therebetween,

said lead electrode having a first thickness region formed in opposing relation to said semiconductor chip and a second thickness region formed externally of said first region to be thinner than said first thickness region.

2. The semiconductor device according to claim 1, wherein said second thickness region has a thickness equal to or smaller than a thickness of said bonding member located between said lead electrode and said semiconductor chip.

3. The semiconductor device according to claim 1, wherein said first thickness region has a thickness equal to or smaller than three times a thickness of said bonding member located between said lead electrode and said semiconductor chip.

4. The semiconductor device according to claim 1, wherein said lead electrode further has a third thickness region thicker than said second thickness region and located externally of said second thickness region.

5. A semiconductor device comprising:

a lead electrode connecting to a lead wire;

a case electrode having a wall portion on an outer peripheral portion thereof; and

a semiconductor chip disposed between said lead electrode and said case electrode with a bonding member interposed therebetween,

said lead electrode having a trenched portion formed in a surface of said lead electrode opposite to a surface thereof opposing said semiconductor chip and extending in a circumferential direction of said electrode.

6. A semiconductor device comprising:

a lead electrode connecting to a lead wire;

a case electrode having a wall portion on an outer peripheral portion thereof; and

a semiconductor chip disposed between said lead electrode and said case electrode with a bonding member interposed therebetween,

said lead electrode having a first region located in a range to be bonded to said semiconductor chip with said bonding member interposed therebetween, a second region thinner than said first region and located at a larger distance from the lead wire than said first region, and a third region thicker than said second region and located at a larger distance from the lead wire than said second region.

7. The semiconductor device according to claim 6, wherein

said second region is formed such that a first distance in a direction connecting an edge of said second region closer to the lead wire and an outer circumferential edge of said second region is equal to or smaller than 0.5 times a distance between an edge of said third region closer to said lead wire and an outer circumferential edge of said third region.

8. The semiconductor device according to claim 6, wherein said second region is formed in a range corresponding to 0.5 times or less a distance between an edge of said third region closer to said lead wire and an outer circumferential edge of said third region.

9. The semiconductor device according to claim 6, wherein said first region is formed to have a thickness equal to or less than three times a thickness of said bonding member bonded to said lead electrode.

10. The semiconductor device according to claim 1, wherein a metal plate is disposed between said lead electrode and said semiconductor chip or between said semiconductor chip and said case electrode.